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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.
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09/577,835 05/25/00 PAN

P M4065.0321/P

EXAMINER

MMC2/0322

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NGIVEN, P

ART UNIT

PAPER NUMBER

2811
DATE MAILED:

03/22/01

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

Office Action Summary

Application No.

09/577,835

Applicant(s)

PAN et al.

Examiner

CUONG Q NGUYEN

Group/Art Unit

2811

—The MAILING DATE of this communication appears on the cover sheet beneath the correspondence address—

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE three MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, such period shall, by default, expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).

Status

- ☐ Responsive to communication(s) filed on _____.
- ☐ This action is **FINAL**.
- ☐ Since this application is in condition for allowance except for formal matters, **prosecution as to the merits is closed** in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11; 453 O.G. 213.

Disposition of Claims

- ☒ Claim(s) 25-30 is/are pending in the application.
Of the above claim(s) _____ is/are withdrawn from consideration.
- ☐ Claim(s) _____ is/are allowed.
- ☒ Claim(s) 25-30 is/are rejected.
- ☐ Claim(s) _____ is/are objected to.
- ☐ Claim(s) _____ are subject to restriction or election requirement.

Application Papers

- ☐ See the attached Notice of Draftsperson's Patent Drawing Review, PTO-948.
- ☐ The proposed drawing correction, filed on _____ is ☐ approved ☐ disapproved.
- ☐ The drawing(s) filed on _____ is/are objected to by the Examiner.
- ☐ The specification is objected to by the Examiner.
- ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. § 119 (a)-(d)

- ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d).
 - ☐ All ☐ Some* ☐ None of the CERTIFIED copies of the priority documents have been received.
 - ☐ received in Application No. (Series Code/Serial Number) _____.
 - ☐ received in this national stage application from the International Bureau (PCT Rule 1.7.2(a)).

*Certified copies not received: _____

Attachment(s)

- ☐ Information Disclosure Statement(s), PTO-1449, Paper No(s). _____
- ☒ Notice of Reference(s) Cited, PTO-892
- ☐ Notice of Draftsperson's Patent Drawing Review, PTO-948
- ☐ Interview Summary, PTO-413
- ☐ Notice of Informal Patent Application, PTO-152
- ☐ Other _____

Office Action Summary

Art Unit: 2811

DETAILED ACTION

1. The preliminary amendment filed on 05/25/00 has been entered.

Oath/Declaration

2. The oath/declaration filed on 05/25/00 is acceptable.

Claim Rejections - 35 U.S.C. § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

Claims 25-29 are rejected under 35 U.S.C. 102(e) as being anticipated by Wu et al. (US 5,925,918).

Regarding claims 25-28, Wu et al. discloses an integrated circuit comprising: a semiconductor wafer (110) having a surface; a gate dielectric film (120) formed on the surface of the wafer; a gate electrode stack having sidewalls formed on the gate dielectric film, wherein the gate electrode stack including a polysilicon layer (430) on the gate dielectric layer, a TiN barrier layer on the polysilicon layer, and a refractory metal layer (a W layer) on the TiN layer; nitride spacers (510) formed on the sidewalls of the gate electrode stack, wherein the spacers extend along the sidewalls of the metal layer, the TiN layer and upper portions of polysilicon layer's sidewalls. See Wei et al.'s Fig.5.

Art Unit: 2811

Regarding claim 29, the Wu et al.'s barrier layer formed of TiN which is the same material for forming barrier of present invention. Therefore, Wu et al.'s barrier layer inherently has the same characteristics as claimed device such as the barrier is substantially impermeable to silicon and metal atoms.

Claim Rejections - 35 U.S.C. § 103

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 25-27 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wei et al. (US 5,304,504) in view of Tehrani et al. (US 5,804,458).

Wei et al. discloses an integrated circuit comprising: a semiconductor wafer (10) having a surface; a gate dielectric film (14) formed on the surface of the wafer; a gate electrode stack having sidewalls formed on the gate dielectric film, wherein the gate electrode stack including a polysilicon layer (16) on the gate dielectric layer, a TiN layer (18) on the polysilicon layer, and a refractory metal layer (22) on the TiN layer; oxide spacers (28) formed on the sidewalls of the gate electrode stack, wherein the spacers extend along the sidewalls of the metal layer (22) and do not extend the sidewalls of polysilicon layer (16). See Wei et al.'s Fig.4.

Art Unit: 2811

Wei et al. does not teach that the spacers formed of nitride.

Tehrani et al. discloses an integrated comprising spacers (22) formed on sidewalls of a gate electrode (20), the spacer (220) formed of oxide or nitride. See Tehrani et al.'s Fig.4 and col.3 lines 35-40.

It would have been obvious to one of ordinary skill in the art to form Wei et al.'s spacers (28) of nitride instead of oxide as taught by Tehrani et al. because material such as oxide and nitride are art recognized equivalent materials to form the gate's sidewall spacers.

Claim 30 is rejected under 35 U.S.C. 103(a) as being unpatentable over Wu et al.

Wu et al. does not teach that the spacer has a thickness of 50-500 angstroms. However, the thickness of spacer is an art recognized variable of importance which is subject to routine experimentation and optimization. Therefore, it would have been obvious to one of ordinary skill in the art to arrive the spacer having the thickness as claimed.

Conclusion

5. Papers related to this application may be submitted to Technology center (TC) 2800 by facsimile transmission. Papers should be faxed to TC 2800 via the TC 2800 Fax center located in Crystal Plaza 4, room 4-C23. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Group 2811 Fax Center number is (703) 308-7722 and 308-7724. The Group 2811 Fax Center is to be used only for papers related to Group 2811 applications.

Art Unit: 2811

6. Any inquiry concerning this communication or any earlier communication from the Examiner should be directed to CUONG Q NGUYEN whose telephone number is (703) 308-1293. The Examiner is in the Office generally between the hours of 6:30 AM to 5:00 PM (Eastern Standard Time) Monday through Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor TOM THOMAS who can be reached on (703) 308-2772. The fax phone number for the organization where this application or proceeding is assigned is (703) 308-7722 or 308-7724.

Any inquiry of a general nature or relating to the status of this application should be directed to the Technology Center Receptionists whose telephone number is 308-0956.

CN

March 19, 2001


TOM THOMAS
SUPERVISORY PATENT EXAMINER